



2N40

Preliminary

Power MOSFET

2 Amps, 400 Volts N-CHANNEL POWER MOSFET

DESCRIPTION

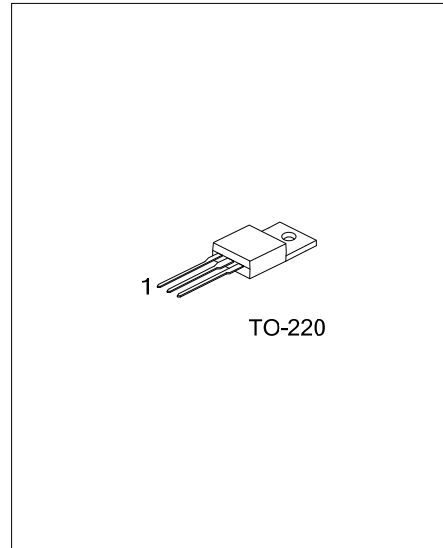
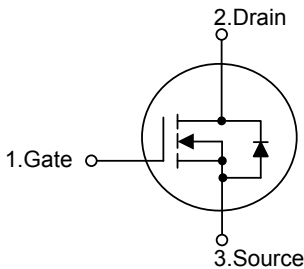
The UTC **2N40** is an N-channel mode power MOSFET using UTC's advanced technology to provide customers with a minimum on-state resistance, stable off-state characteristics and superior switching performance. It also can withstand high energy pulse in the avalanche.

The UTC **2N40** is usually used in general purpose switching applications, motor control circuits and switched mode power supply.

FEATURES

- * High switching speed
- * 2A, 400V, $R_{DS(ON)}=3.5\Omega @ V_{GS}=10V$
- * 100% avalanche tested

SYMBOL



ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
2N40L-TA3-T	2N40G-TA3-T	TO-220	G	D	S	Tube

Note: Pin Assignment: G: Gate D: Drain S: Source

	<p>(1) T: Tube</p> <p>(2) TA3: TO-220</p> <p>(3) G: Halogen Free, L: Lead Free</p>
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■ ABSOLUTE MAXIMUM RATINGS ($T_C=25^\circ\text{C}$, unless otherwise noted)

PARAMETER	SYMBOL	RATINGS	UNIT
Drain-Source Voltage	V_{DSS}	400	V
Gate-Source Voltage	V_{GSS}	± 30	V
Drain Current	Continuous	I_D	2
	Pulsed	I_{DM}	7
Avalanche Current	I_{AR}	2.5	A
Single Pulsed Avalanche Energy	E_{AS}	100	mJ
Power Dissipation	P_D	25	W
Linear Derating Factor	$\Delta P_D / \Delta T_{mb}$	0.2	W/ $^\circ\text{C}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature Range	T_{STG}	-55~150	$^\circ\text{C}$

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL CHARACTERISTICS

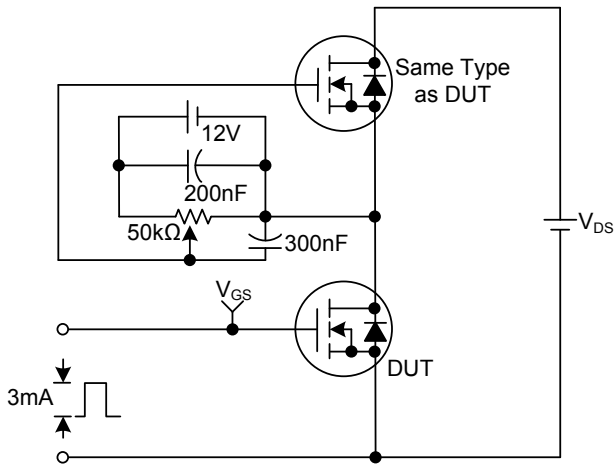
PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	θ_{JA}	62.5	$^\circ\text{C}/\text{W}$
Junction to Case	θ_{JC}	5	$^\circ\text{C}/\text{W}$

■ ELECTRICAL CHARACTERISTICS ($T_J=25^\circ\text{C}$, unless otherwise specified)

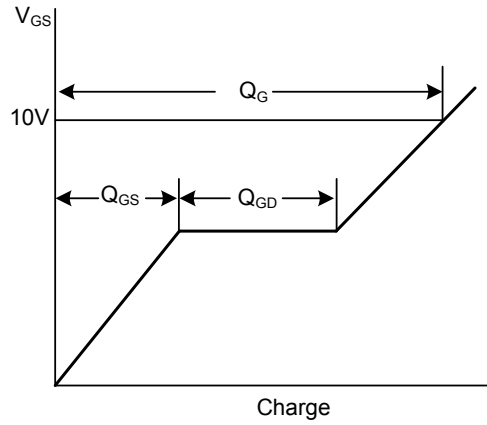
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$I_D=250\mu\text{A}$, $V_{GS}=0\text{V}$	400			V
Breakdown Voltage Temperature Coefficient	$\Delta BV_{DSS}/\Delta T_J$	$V_{DS}=V_{GS}$, $I_D=250\mu\text{A}$		0.45		$V/^\circ\text{C}$
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=400\text{V}$, $V_{GS}=0\text{V}$		1	25	μA
Gate- Source Leakage Current	Forward	$V_{GS}=+30\text{V}$, $V_{DS}=0\text{V}$		+10	+200	nA
	Reverse	$V_{GS}=-30\text{V}$, $V_{DS}=0\text{V}$		-10	-200	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS}=V_{GS}$, $I_D=250\mu\text{A}$	2.0	3.0	4.0	V
Static Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10\text{V}$, $I_D=1.25\text{A}$		2.0	3.5	Ω
DYNAMIC PARAMETERS						
Input Capacitance	C_{ISS}	$V_{GS}=0\text{V}$, $V_{DS}=25\text{V}$, $f=1.0\text{MHz}$		240		pF
Output Capacitance	C_{OSS}			44		pF
Reverse Transfer Capacitance	C_{RSS}			26		pF
SWITCHING PARAMETERS						
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS}=10\text{V}$, $V_{DS}=320\text{V}$, $I_D=2.5\text{A}$		20	25	nC
Gate to Source Charge	Q_{GS}			2	3	nC
Gate to Drain Charge	Q_{GD}			8	12	nC
Turn-ON Delay Time	$t_{D(ON)}$	$V_{DD}=200\text{V}$, $I_D=2.5\text{A}$, $R_G=24\Omega$, $R_D=78\Omega$		10		ns
Rise Time	t_R			25		ns
Turn-OFF Delay Time	$t_{D(OFF)}$			46		ns
Fall-Time	t_F			25		ns
Internal Drain Inductance	L_D	Measured from drain lead 6 mm from package to centre of die		4.5		nH
Internal Source Inductance	L_S	Measured from source lead 6 mm from package to source bond pad		7.5		nH
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Maximum Body-Diode Continuous Current	I_S	$T_C=25^\circ\text{C}$			2.5	A
Maximum Body-Diode Pulsed Current	I_{SM}				10	A
Drain-Source Diode Forward Voltage	V_{SD}	$I_S=2.5\text{A}$, $V_{GS}=0\text{V}$			1.2	V
Body Diode Reverse Recovery Time	t_{RR}	$I_S=2.5\text{A}$, $V_{GS}=0\text{V}$, $dI/dt=100\text{A}/\mu\text{s}$		200		ns
Body Diode Reverse Recovery Charge	Q_{RR}			2.0		μC

■ TEST CIRCUITS AND WAVEFORMS

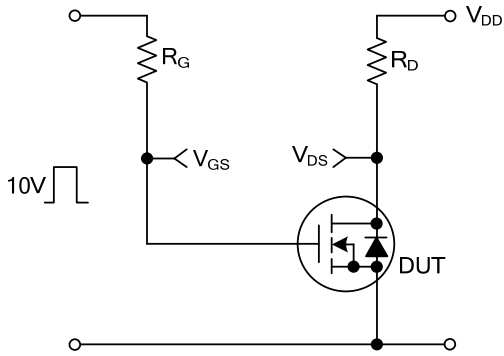
Gate Charge Test Circuit



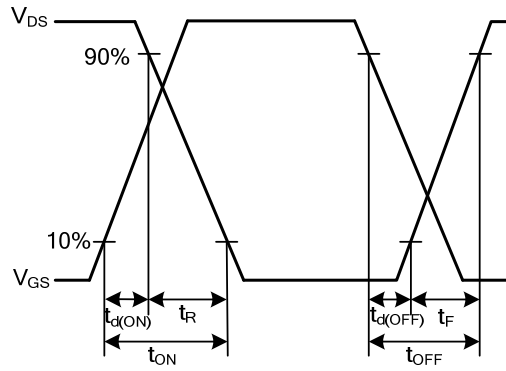
Gate Charge Waveforms



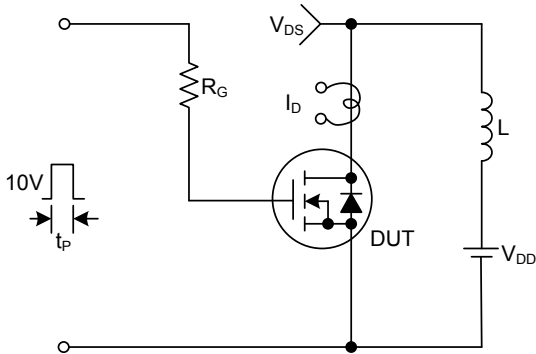
Resistive Switching Test Circuit



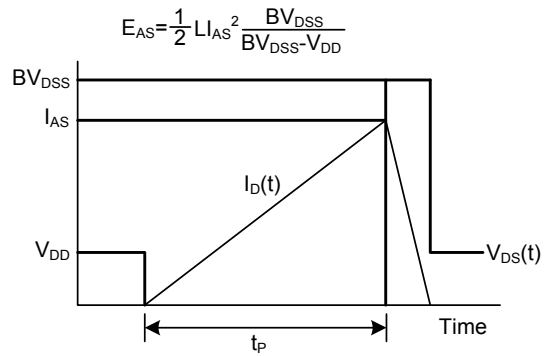
Resistive Switching Waveforms



Unclamped Inductive Switching Test Circuit

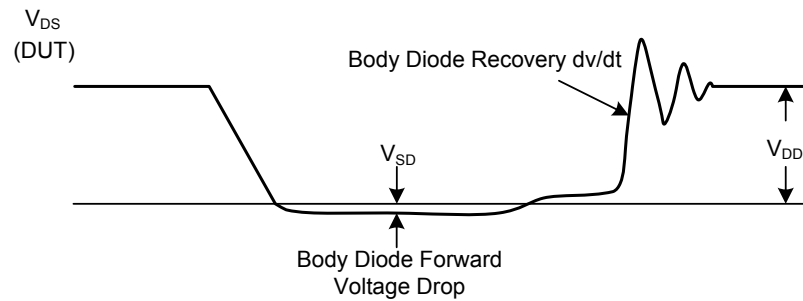
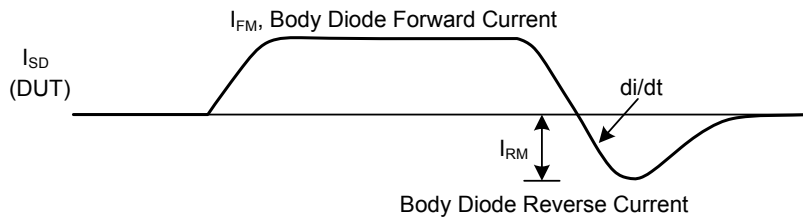
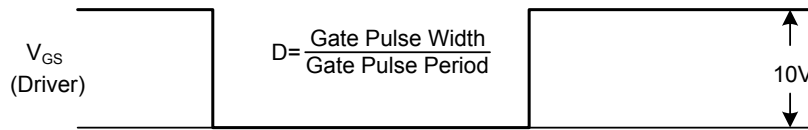
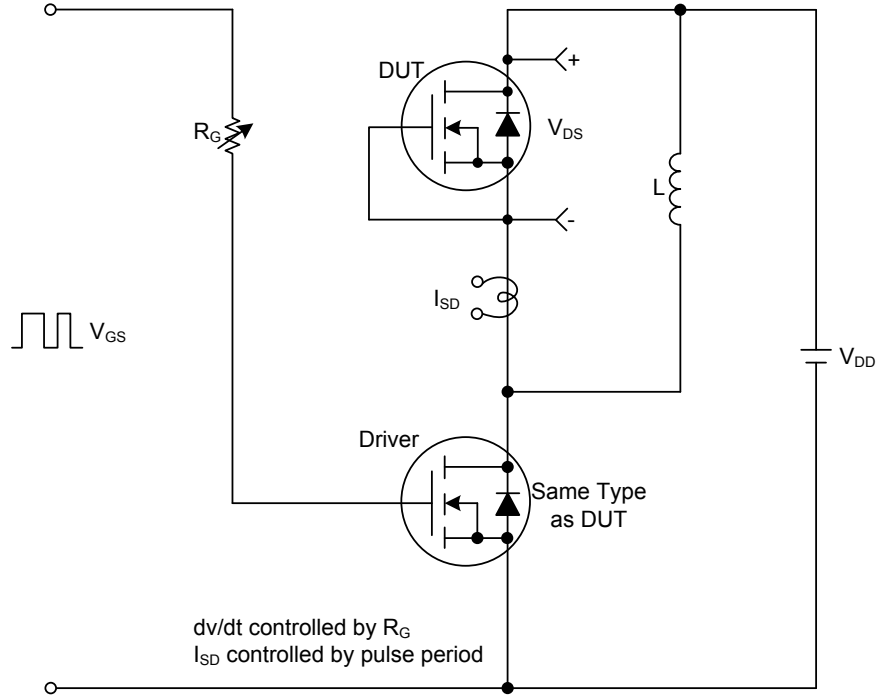


Unclamped Inductive Switching Waveforms



■ TEST CIRCUITS AND WAVEFORMS(Cont.)

Peak Diode Recovery dv/dt Test Circuit & Waveforms



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